



## N-Channel 200-V (D-S) MOSFET

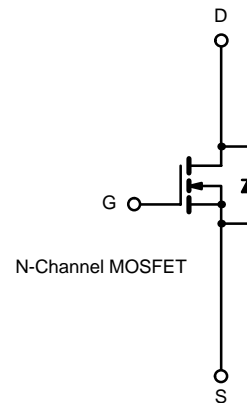
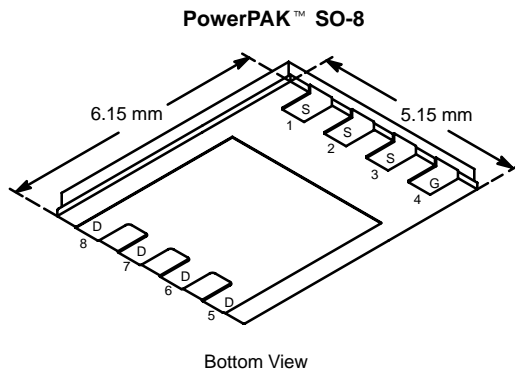
PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
200	0.080 @ $V_{GS} = 10$ V	5.3
	0.090 @ $V_{GS} = 6$ V	5.0

### FEATURES

- TrenchFET® Power MOSFETS
- New Low Thermal Resistance PowerPAK™ Package with Low 1.07-mm Profile
- PWM Optimized for Fast Switching

### APPLICATIONS

- Primary Side Switch for High Density DC/DC
- Telecom/Server 48-V DC/DC
- Industrial and 42-V Automotive



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	10 secs	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	200		V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$			
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>a</sup>	$I_D$	$T_A = 25^\circ\text{C}$	5.3	3.2	A
		$T_A = 70^\circ\text{C}$	4.3	2.6	
Pulsed Drain Current	$I_{DM}$	40			
Avalanche Current	$I_{AS}$	15			
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	4.3	1.6		
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25^\circ\text{C}$	5.2	1.9	W
		$T_A = 70^\circ\text{C}$	3.3	1.2	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	$t \leq 10$ sec	19	24	$^\circ\text{C/W}$
		Steady State	52	65	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	1.5	1.8		

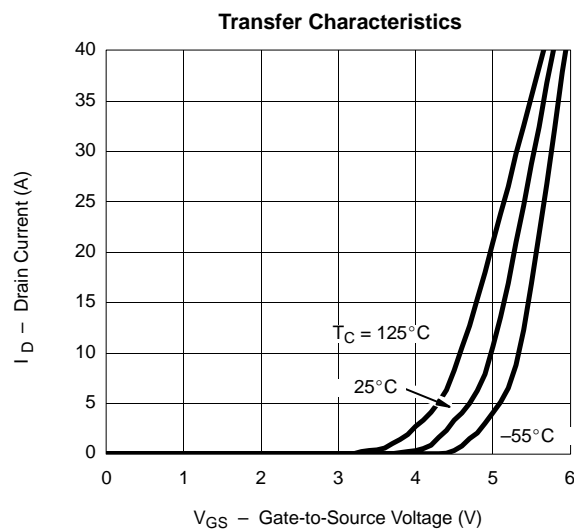
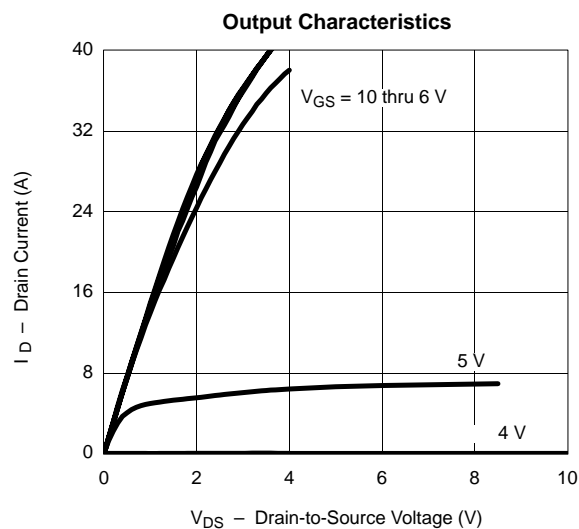
Notes  
a. Surface Mounted on 1" x 1" FR4 Board.

**SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.0			V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 160 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 160 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			5	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	40			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.0 A		0.065	0.080	Ω
		V <sub>GS</sub> = 6.0 V, I <sub>D</sub> = 4.0 A		0.070	0.090	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 5 A		19		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 2.8 A, V <sub>GS</sub> = 0 V		0.75	1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.0 A		34	42	nC
Gate-Source Charge	Q <sub>gs</sub>			7.5		
Gate-Drain Charge	Q <sub>gd</sub>			12.0		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 100 V, R <sub>L</sub> = 25 Ω I <sub>D</sub> = 4.0 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 6 Ω		14	20	ns
Rise Time	t <sub>r</sub>			20	30	
Turn-Off Delay Time	t <sub>d(off)</sub>			32	50	
Fall Time	t <sub>f</sub>			25	35	
Gate Resistance	R <sub>g</sub>				0.85	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.8 A, di/dt = 100 A/μs		70	100	ns

## Notes

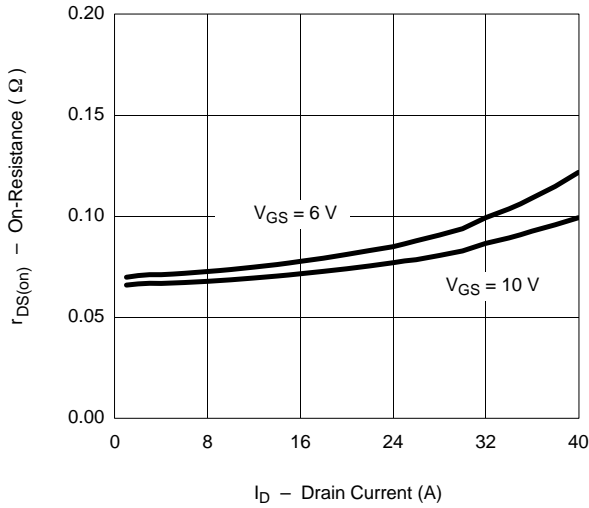
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.  
b. Guaranteed by design, not subject to production testing.

**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**

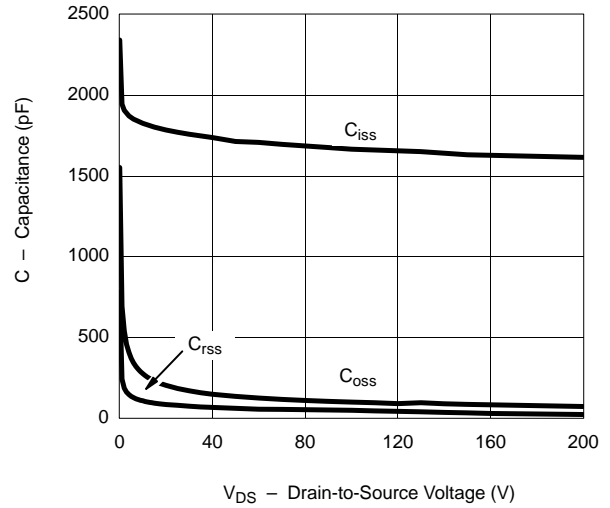


**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

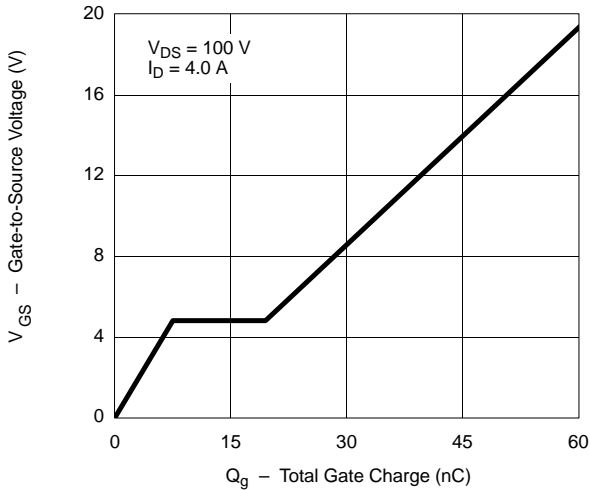
On-Resistance vs. Drain Current



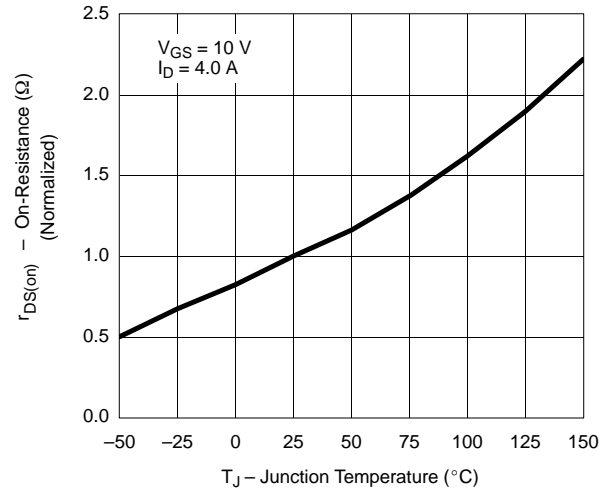
Capacitance



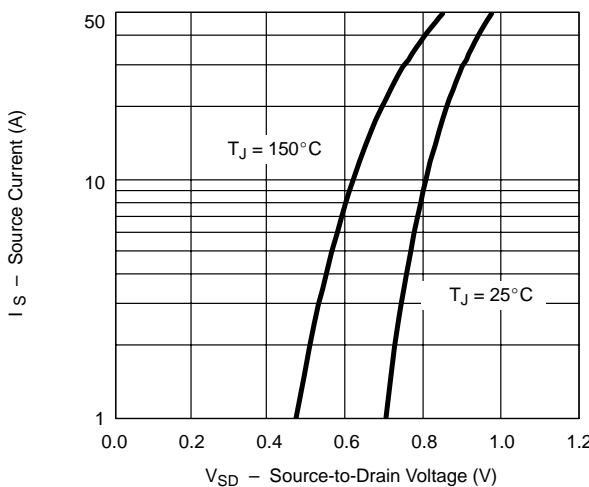
Gate Charge



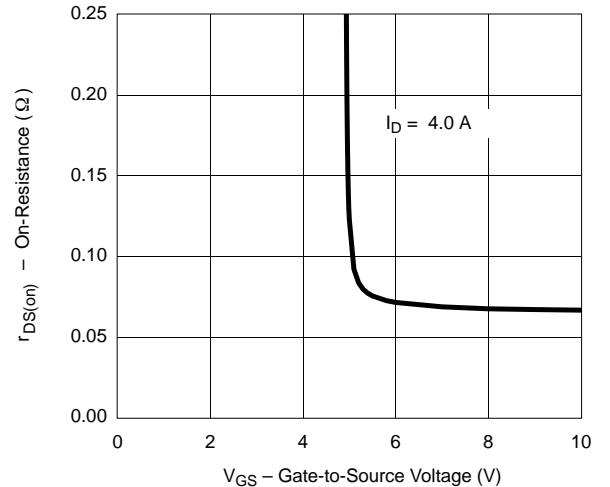
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

